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could

a plurality of first thin film transistors for switching said pixel electrodes and formed over said substrate;

a driver circuit formed over said substrate for driving said plurality of first thin film transistors, said driver circuit comprising at least one second thin film transistor;

each of said first thin film transistors and said second thin film transistor comprising:

a semiconductor film comprising silicon and including at least one channel region;

a gate insulating film adjacent to said channel region; and

a gate electrode adjacent to said gate insulating film,

wherein the semiconductor film of said second thin film transistor contains germanium and the semiconductor film of the first thin film transistors is not intentionally added with germanium and a concentration of germanium in the semiconductor film of the second thin film transistor is higher than a concentration of germanium in the semiconductor film of the first thin film transistor.

Please add the following new claims:

44 (New). The semiconductor device according to claim 1 wherein each of the first active layer and the second active layer further comprises a metal selected from the group consisting of nickel, iron, cobalt and platinum.

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45 (New). The semiconductor device according to claim 2 wherein each of the first active layer and the second active layer further comprises a metal selected from the group consisting of nickel, iron, cobalt and platinum.

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46 (New). The semiconductor device according to claim 30 wherein each of the semiconductor films of the first and second thin film transistors further comprises a metal selected from the group consisting of nickel, iron, cobalt and platinum.

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concl
47 (New). The semiconductor device according to claim 30 wherein each of the first and second semiconductor films further comprises a metal selected from the group consisting of nickel, iron, cobalt and platinum.

48 (New). The semiconductor device according to claim 36 wherein each of the first and second semiconductor films further comprises a metal selected from the group consisting of nickel, iron, cobalt and platinum.

REMARKS

Applicants have the following remarks in response to the Office Action of January 28, 2002.

§112, First Paragraph Rejections

In the Office Action, the Examiner rejects Claims 30-38 and 41-43 under 35 USC §112, first paragraph, as allegedly

“...containing subject matter which was not described in the specification in such a way as to reasonably convey to one skilled in the relevant art that the inventor(s), at the time the application was filed, had possession of the claimed invention.”

In particular, the Examiner contends that the specification does not describe first and second thin film transistors wherein the semiconductor film of the second thin film transistor contains germanium at a higher concentration than the semiconductor film of said first thin film transistors